

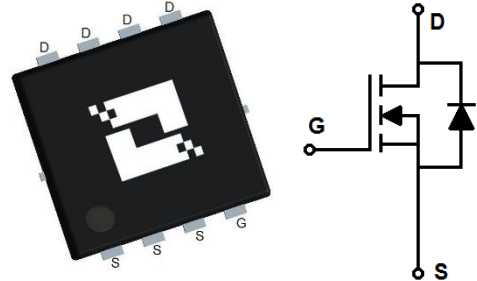
Features

- Low $R_{DS(on)}$ @ $V_{GS}=10V$
- 5V Logic Level Control
- 100% UIS Tested
- Pb-Free, RoHS Compliant

$V_{(BR)DSS}$	$R_{DS(ON)}$ Typ	I_D Max
30V	2.8m Ω @10V	78A
	5.0m Ω @4.5V	

Applications

- Load Switch
- Switching Circuits
- High Speed line Driver
- Power management


PDFN3X3
Order Information

Product	Package	Marking	Packing
DWT3R203M	PDFN3X3	3R203M	5000PCS/Reel

Absolute Maximum Ratings

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Symbol	Parameter	Rating	Unit
Common Ratings ($T_A=25^\circ\text{C}$ Unless Otherwise Noted)			
V_{GS}	Gate-Source Voltage	± 20	V
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	30	V
T_J	Maximum Junction Temperature	150	$^\circ\text{C}$
T_{STG}	Storage Temperature Range	-50 to 150	$^\circ\text{C}$
Mounted on Large Heat Sink			
I_{DM}	Pulse Drain Current Tested①	$T_A=25^\circ\text{C}$	300
I_D	Continuous Drain Current	$T_A=25^\circ\text{C}$	78
		$T_A=70^\circ\text{C}$	62
P_D	Maximum Power Dissipation	$T_A=25^\circ\text{C}$	52
EAS	Avalanche energy, single pulsed ②		100
$R_{\theta JC}$	Thermal Resistance Junction-Ambient		2.4

Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Electrical Characteristics @ T_J = 25°C (unless otherwise stated)						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V I _D =250μA	30	--	--	V
I _{DSS}	Zero Gate Voltage Drain Current(T _A =25°C)	V _{DS} =30V, V _{GS} =0V	--	--	1	μA
	Zero Gate Voltage Drain Current(T _A =125°C)	V _{DS} =24V, V _{GS} =0V	--	--	100	nA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±20V, V _{DS} =0V	--	--	±100	nA
V _{GS(TH)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	1.0	1.6	2.5	V
R _{DS(ON)}	Drain-Source On-State Resistance ^②	V _{GS} =10, I _D =20A	--	2.8	3.6	mΩ
R _{DS(ON)}	Drain-Source On-State Resistance ^②	V _{GS} =4.5V, I _D =15A	--	5.0	5.9	mΩ
Dynamic Electrical Characteristics @ T_J = 25°C (unless otherwise stated)						
C _{iss}	Input Capacitance	V _{DS} =15V, V _{GS} =0V, f=1MHz	--	1040	--	pF
C _{oss}	Output Capacitance		--	623	--	pF
C _{rss}	Reverse Transfer Capacitance		--	26	--	pF
Q _g	Total Gate Charge	V _{DS} =15V I _D =20A, V _{GS} =10V	--	17.8	--	nC
Q _{gs}	Gate Source Charge		--	2.2	--	nC
Q _{gd}	Gate Drain Charge		--	4.5	--	nC
Switching Characteristics						
t _{d(on)}	Turn on Delay Time	V _{DD} =15V, I _D =1A, R _G =3.3Ω, V _{GS} =10V	--	10	--	ns
t _r	Turn on Rise Time		--	21	--	ns
t _{d(off)}	Turn Off Delay Time		--	32	--	ns
t _f	Turn Off Fall Time		--	12	--	ns
Source Drain Diode Characteristics						
I _{SD}	Source drain current(Body Diode)	T _A =25°C	--	--	80	A
V _{SD}	Forward on voltage ^②	T _J =25°C, I _{SD} =10A, V _{GS} =0V	--	0.78	1.2	V

Notes:

① Pulse width limited by maximum allowable junction temperature ②Pulse test ; Pulse width≤300μs, duty cycle≤2%.

Typical Characteristics

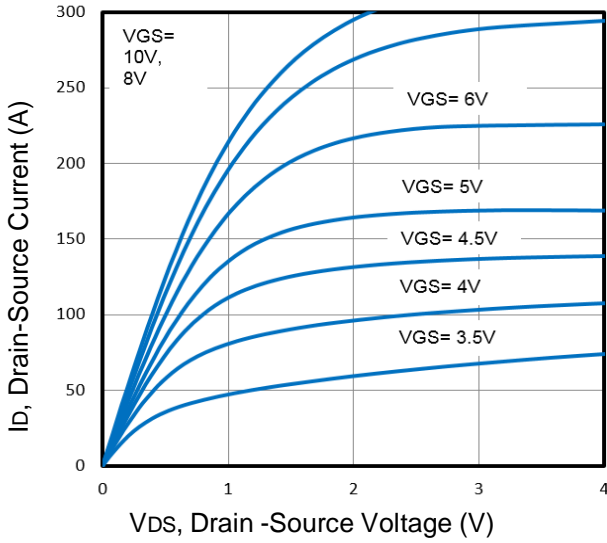


Fig1. Typical Output Characteristics

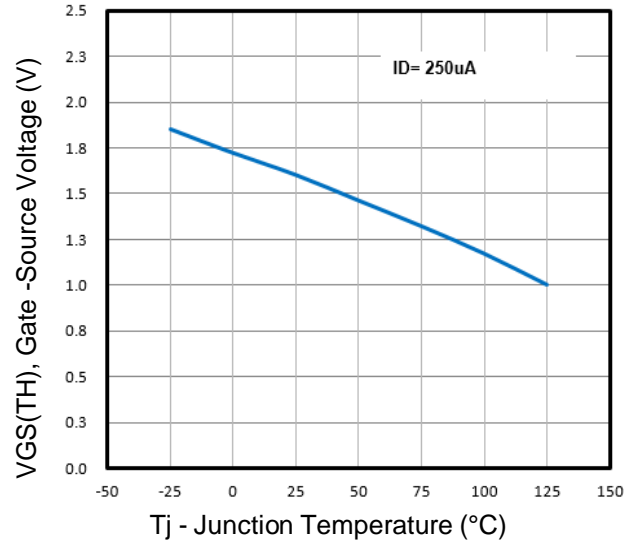


Fig2. Normalized Threshold Voltage Vs. Temperature

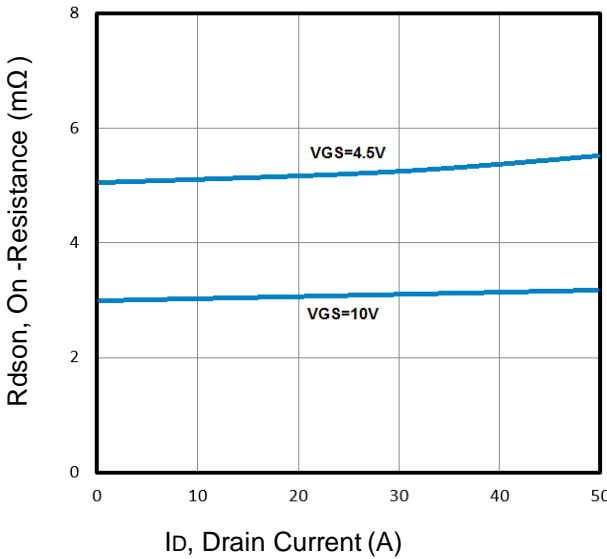


Fig3. On-Resistance vs. Drain Current and Gate

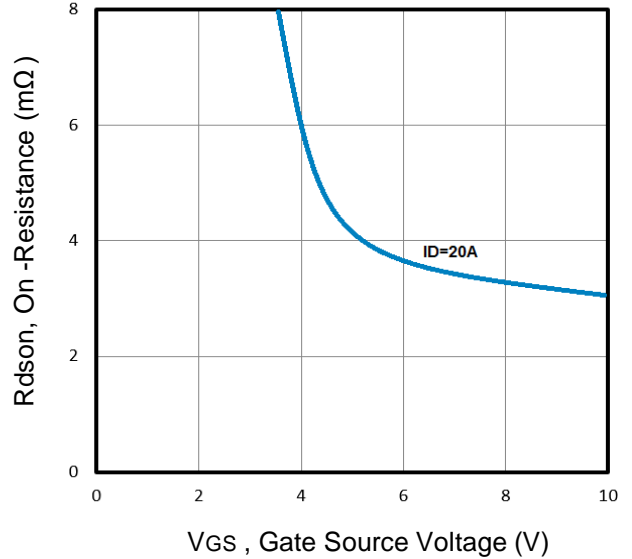


Fig4. On-Resistance vs. Gate Source Voltage

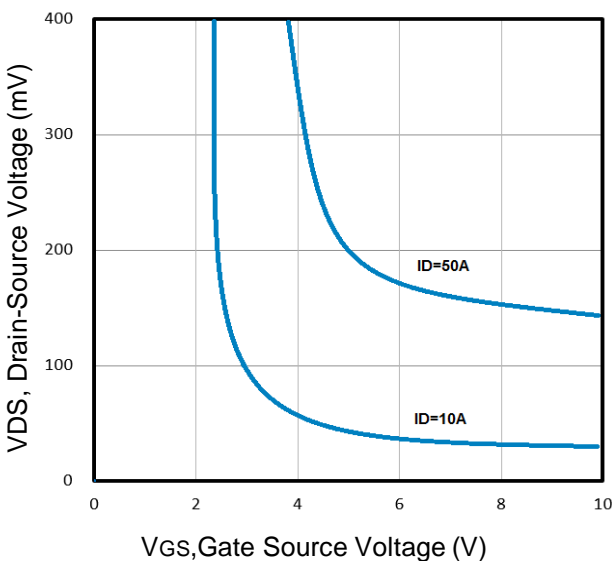


Fig5. Drain-Source Voltage vs Gate-Source Voltage

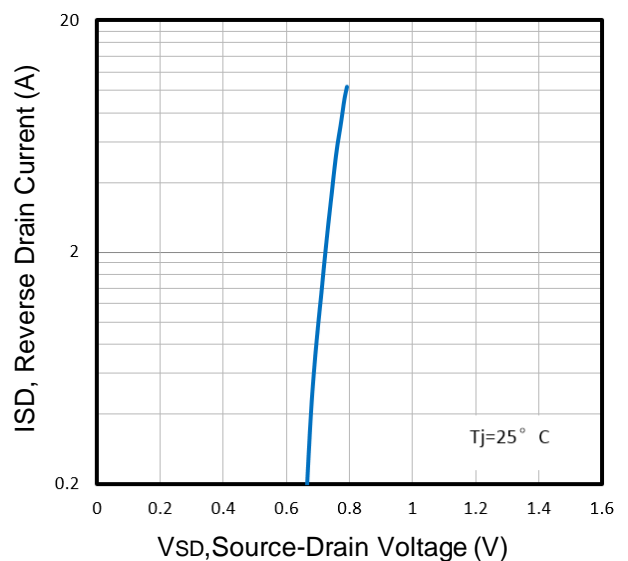


Fig6. Typical Source-Drain Diode Forward Voltage

Typical Characteristics

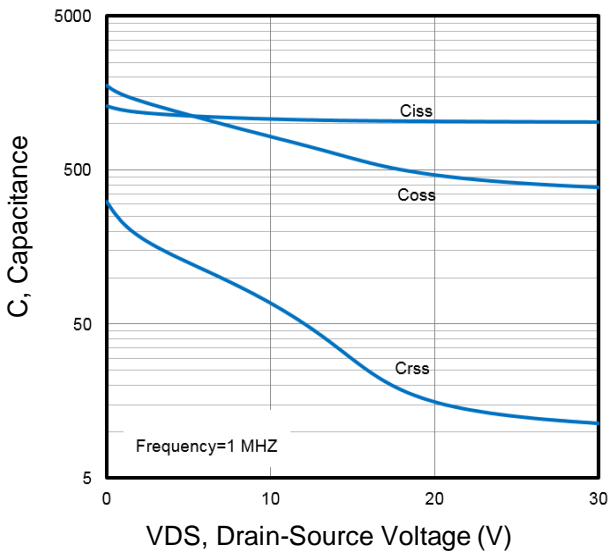


Fig7. Typical Capacitance Vs. Drain-Source Voltage

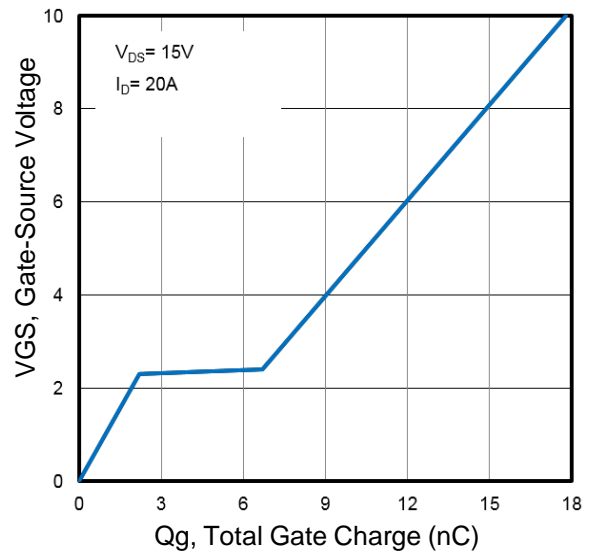


Fig8. Typical Gate Charge Vs. Gate-Source Voltage

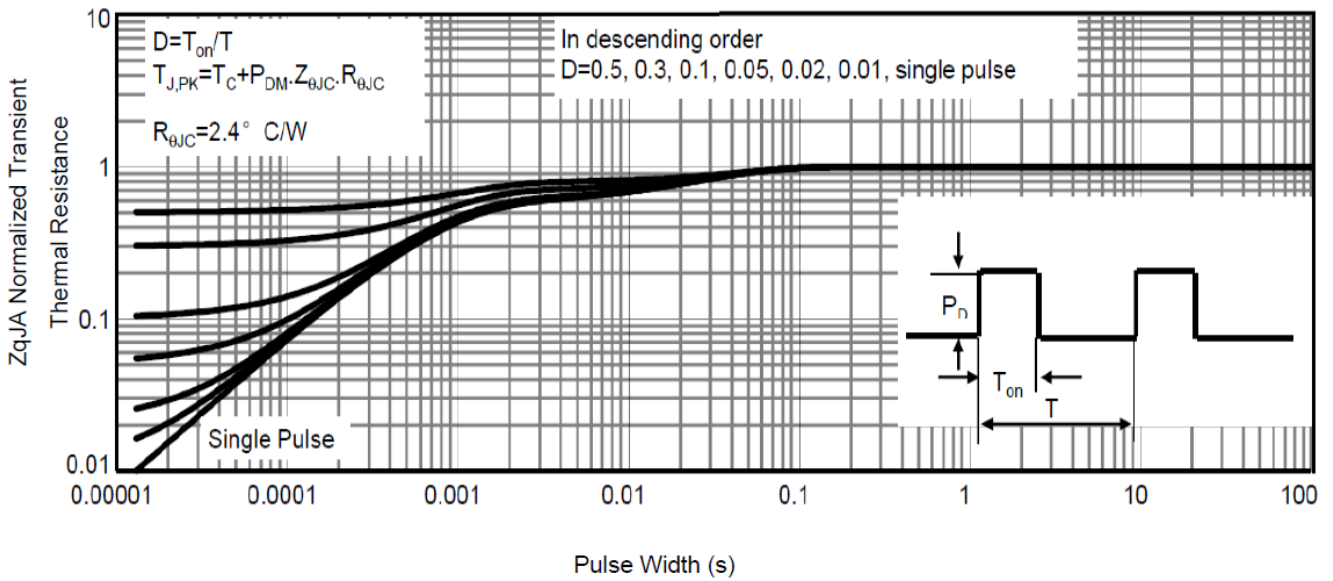


Fig9. Normalized Maximum Transient Thermal Impedance

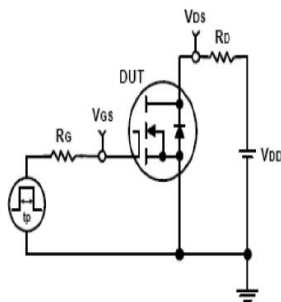


Fig10. Switching Time Test Circuit and waveforms

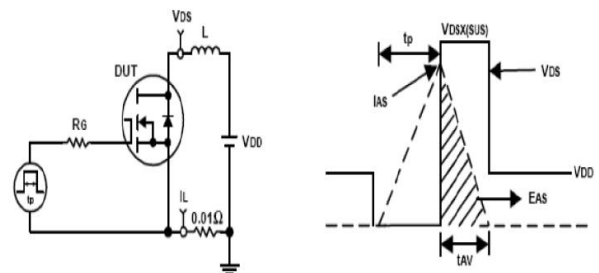
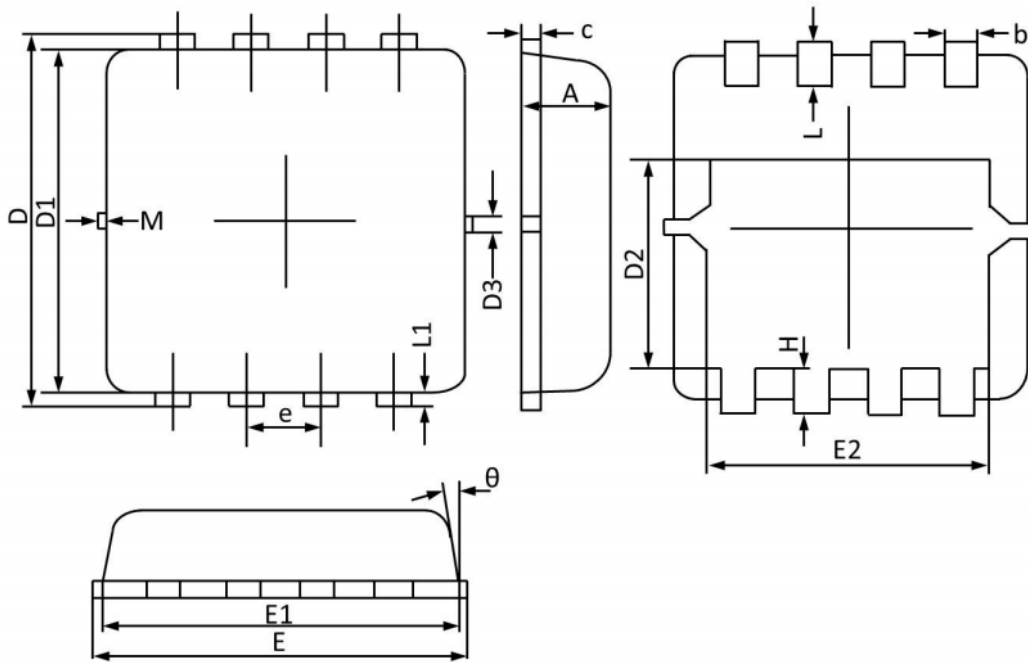


Fig11. Unclamped Inductive Test Circuit and waveforms

PDFN3X3 Mechanical Data



DIMENSIONS (unit : mm)

Symbol	Min	Typ	Max	Symbol	Min	Typ	Max
A	0.70	0.75	0.80	b	0.25	0.30	0.35
C	0.10	0.15	0.25	D	3.25	3.35	3.45
D1	3.00	3.10	3.20	D2	1.78	1.88	1.98
D3	--	0.13	--	E	3.20	3.30	3.40
E1	3.00	3.15	3.20	E2	2.39	2.49	2.59
e	0.65BSC			H	0.30	0.39	0.50
L	0.30	0.40	0.50	L1	--	0.13	--
θ	--	10°	12°	M	*	*	0.15

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